



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Examiner: Tuan M. Nguyen

Toshiya Fukuhisa, et al.

Group Art Unit: 2828

Serial No. 09/515,285

Filed: February 29, 2000

For: SEMICONDUCTOR LASER AND A

MANUFACTURING METHOD FOR THE

SAME

October 23, 2002

Irvine, California 92614

## RESPONSE TO OFFICE ACTION

Assistant Commissioner for Patents Washington, D.C. 20231

Dear Sir:

In response to the Office Action mailed July 31, 2002, please amend the above-identified application as follows:

## **IN THE CLAIMS**

Please add the following new claims:

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37. (New) A semiconductor laser according to Claim 2,

wherein the second layer is co-doped with p-type impurities and n-

type impurities and has substantially n-type conductivity, and such that the concentration

4 of n-type carriers is N2.

1 38. (New) A semiconductor laser manufacturing method according to Claim

2 26,

wherein the first process co-dopes the second layer with p-type

4 impurities and n-type impurities, such that the concentration of n-type carriers is N2.

10/30/2002 NMOHAMM1 00000031 09515285

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